

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	(test\$3 near (memory semiconductor circuit)) and ((first and second) near (select\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 15:38
		(test\$3 near (memory semiconductor circuit)) and (first and second) near (select\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 09:51
		"5668764".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/23 13:11
S2	2	"5668764".pn. and (integrated circuit device internal plurality signal signals select\$3 control\$4 path paths external\$2 input output pad)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/23 13:12
S3	2	"5668764".pn. and (integrated circuit device internal plurality signal signals select\$3 control\$4 path paths external\$2 input output pad pads)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/23 15:54
S4	1896	((flag near indicat\$3) error\$2) near (header)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/02/23 15:55
S5	2	"5668764".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/02/25 14:40
S7	1948	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:08
S8	212	((test\$3 monitor\$3) near (memory semiconductor circuit)) same ((first and second) near (select\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 17:12
S9	22	((test\$3 monitor\$3) near (memory semiconductor circuit)) same ((first and second) near (select\$3))) and ((input output) near (pads))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 17:24

S10	105	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and ((input output) near (pads))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 17:24
S11	1	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/746.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:09
S12	57	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/718.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:09
S13	63	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/724.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:09
S14	24	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/727.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:09
S15	6	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/730.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:09
S16	8	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/742.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:09
S17	22	((test\$3 monitor\$3) near (memory semiconductor circuit)) and ((first and second) near (select\$3)) and 714/738.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 18:10
S18	2	"6594802".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/30 19:13
S19	2	"6484260".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 14:13

S20	1408	(test\$3 near (memory semiconductor circuit)) and ((first and second) near (select\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/05 15:38
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